

HiPerFET™

Power MOSFETs

Q-Class

IXFH 36N55Q
IXFT 36N55Q

V_{DSS} = 550 V
I_{D25} = 36 A
R_{DS(on)} = 0.16 Ω

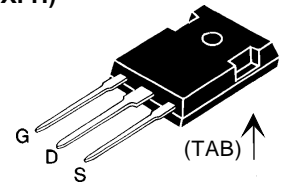
t_{rr} ≤ 250 ns

N-Channel Enhancement Mode
Avalanche Rated, Low Q_g, High dv/dt

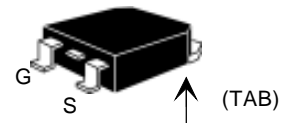


Symbol	Test Conditions	Maximum Ratings	
V _{DSS}	T _J = 25°C to 150°C	550	V
V _{DGR}	T _J = 25°C to 150°C; R _{GS} = 1 MΩ	550	V
V _{GS}	Continuous	±30	V
V _{GSM}	Transient	±40	V
I _{D25}	T _C = 25°C	36	A
I _{DM}	T _C = 25°C, pulse width limited by T _{JM}	148	A
I _{AR}	T _C = 25°C	36	A
E _{AR}	T _C = 25°C	50	mJ
E _{AS}		2.0	mJ
dv/dt	I _S ≤ I _{DM} , di/dt ≤ 100 A/μs, V _{DD} ≤ V _{DSS} , T _J ≤ 150°C, R _G = 2 Ω	20	V/ns
P _D	T _C = 25°C	500	W
T _J		-55 to +150	°C
T _{JM}		150	°C
T _{stg}		-55 to +150	°C
T _L	1.6 mm (0.063 in) from case for 10 s	300	°C
M _d	Mounting torque	1.13/10	Nm/lb.in.
Weight	TO-247	6	g
	TO-268	4	g

TO-247 AD (IXFH)



TO-268 (D3) (IXFT)



G = Gate D = Drain
S = Source TAB = Drain

Features

- IXYS advanced low Q_g process
- Low gate charge and capacitances
 - easier to drive
 - faster switching
- International standard packages
- Low R_{DS(on)}
- Rated for unclamped Inductive load switching (UIS) rated
- Molding epoxies meet UL 94 V-0 flammability classification

Advantages

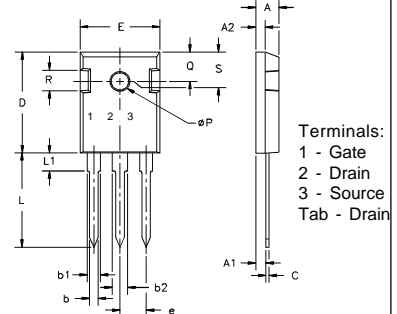
- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values (T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
V _{DSS}	V _{GS} = 0 V, I _D = 250 μA	550		V
V _{GS(th)}	V _{DS} = V _{GS} , I _D = 4 mA	2.5		V
I _{GSS}	V _{GS} = ±30 V _{DC} , V _{DS} = 0			±100 nA
I _{DSS}	V _{DS} = V _{DSS} , V _{GS} = 0 V			25 μA 1 mA
R _{DS(on)}	V _{GS} = 10 V, I _D = 0.5 I _{D25} Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			0.16 Ω

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 20\text{ V}; I_D = 0.5 \cdot I_{D25}$, pulse test	22	33	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		4500	pF
C_{oss}			600	pF
C_{rss}			160	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 2.0\ \Omega$ (External),		17	ns
t_r			18	ns
$t_{d(off)}$			54	ns
t_f			15	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		128	nC
Q_{gs}			26	nC
Q_{gd}			56	nC
R_{thJC}	(TO-247)		0.25	K/W
R_{thCK}				K/W

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$		36	A
I_{SM}	Repetitive; pulse width limited by T_{JM}		148	A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$		1.5	V
t_{rr}	$I_F = 25\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$		1.0	ns
Q_{RM}			10	μC
I_{RM}				A

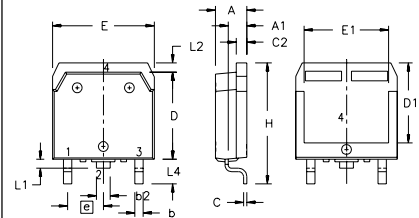
TO-247 AD (IXFH) Outline



Terminals:
1 - Gate
2 - Drain
3 - Source
Tab - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

TO-268 Outline



Terminals: 1 - Gate
2 - Drain
3 - Source
Tab - Drain

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e		.215 BSC		5.45 BSC
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010	BSC	0.25	BSC
L4	.150	.161	3.80	4.10

IXYS reserves the right to change limits, test conditions, and dimensions.

Fig. 1. Output Characteristics
@ 25 Deg. C

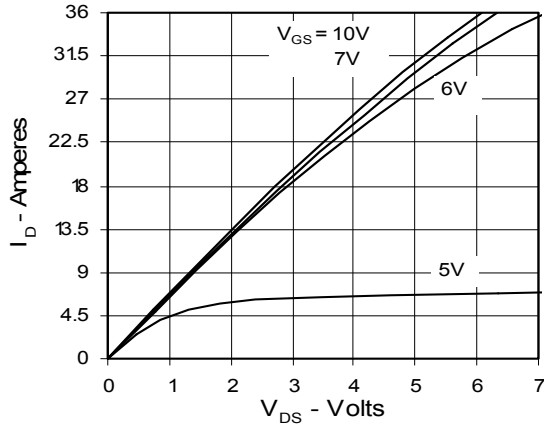


Fig. 2. Extended Output Characteristics
@ 25 deg. C

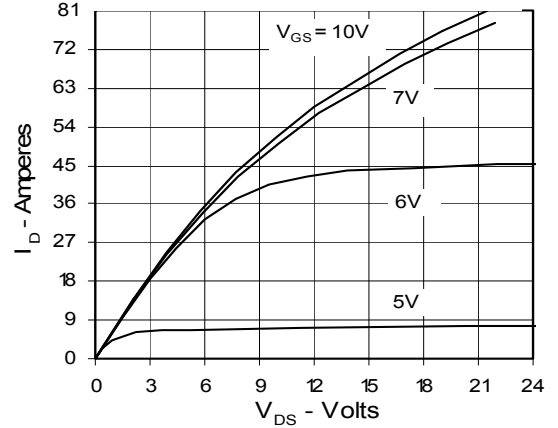


Fig. 3. Output Characteristics
@ 125 Deg. C

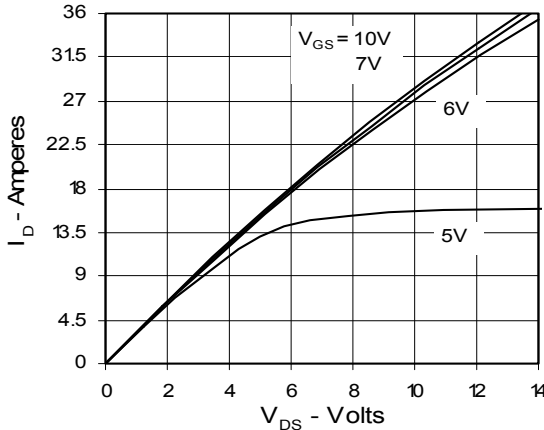


Fig. 4. R_DS(on) Normalized to I_D25 Value vs. Junction Temperature

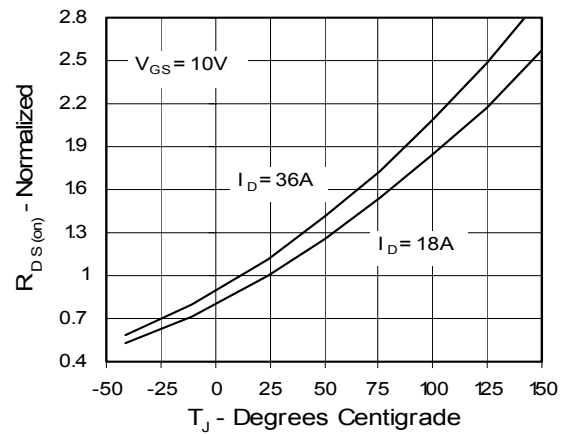


Fig. 5. R_DS(on) Normalized to I_D25 Value vs. I_D

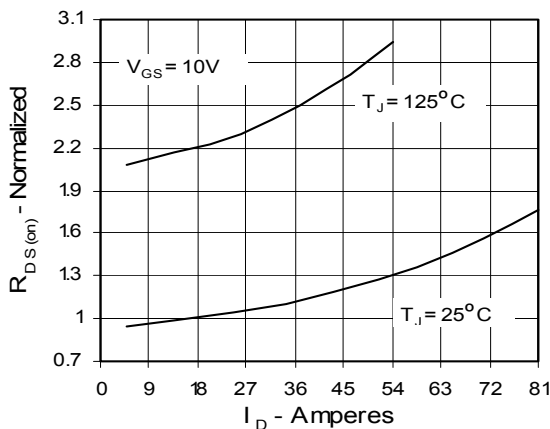


Fig. 6. Drain Current vs. Case Temperature

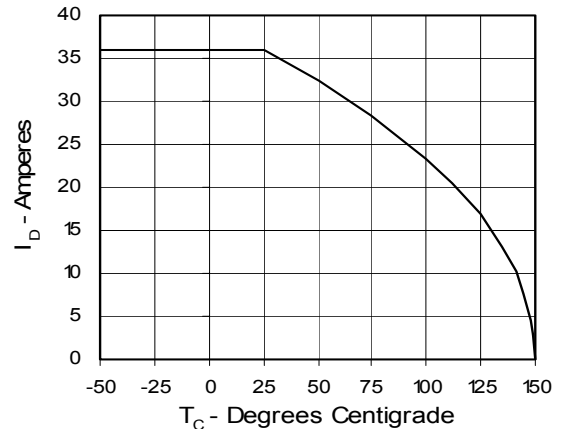


Fig. 7. Input Admittance

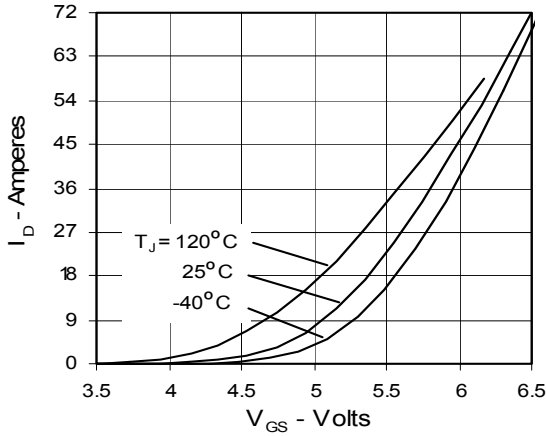


Fig. 8. Transconductance

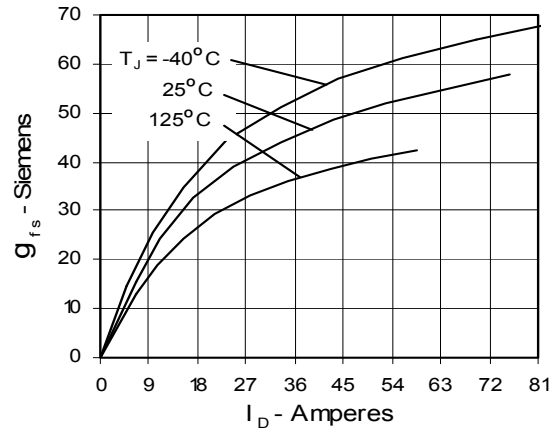


Fig. 9. Source Current vs. Source-To-Drain Voltage

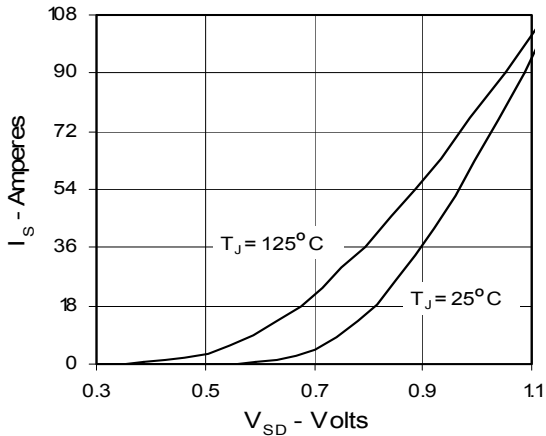


Fig. 10. Gate Charge

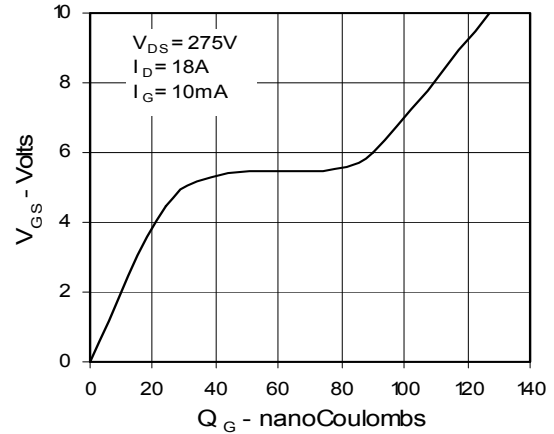


Fig. 11. Capacitance

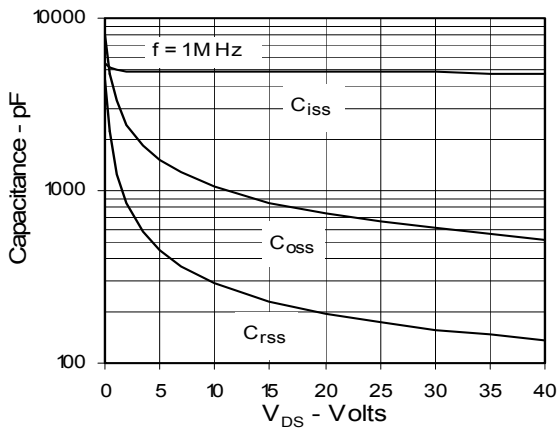
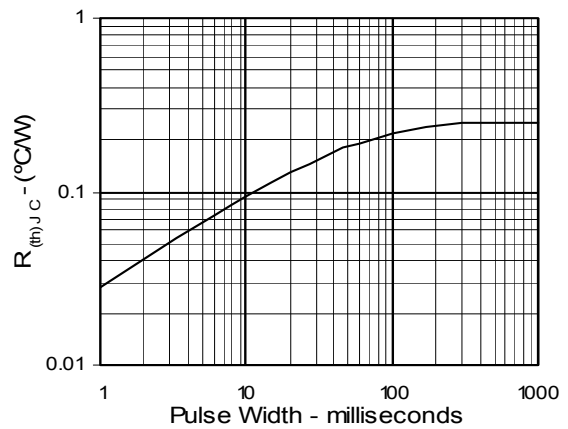


Fig. 12. Maximum Transient Thermal Resistance



IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 6,306,728B1 6,259,123B1 6,306,728B1
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025 6,404,065B1 6,162,665 6,534,343